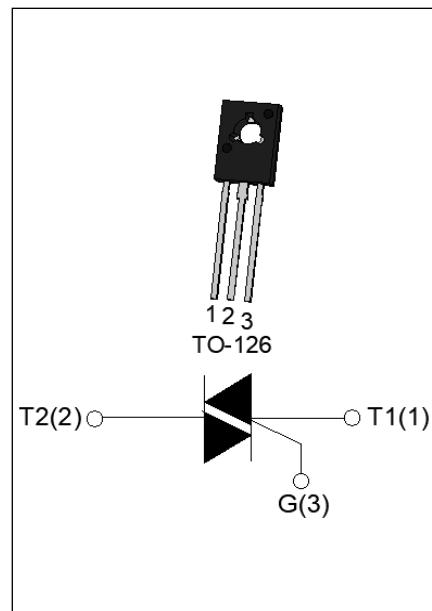


**DESCRIPTION:**

The JST136Q-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-126 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(\text{RMS})}$	4	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{G(T_{I/II/III/IV})}$	10/10/10/25	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 83^\circ\text{C}$)	$I_{T(\text{RMS})}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	35	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		38.5	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	6.1	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dl/dt	80	$\text{A}/\mu\text{s}$
		40	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(\text{AV})}$	0.5	W
Peak gate power	P_{GM}	5	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX.	10	mA
		IV		25	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	20	mA
		II -IV		30	
I_H	$I_T=100\text{mA}$		MAX.	25	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=110^\circ\text{C}$		MIN.	250	V/ μs
$(dV/dt)c$	$(dI/dt)c=1.8\text{A/ms}$, $T_j=110^\circ\text{C}$		MIN.	6	V/ μs
t_{on}	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	1.5	μs	
			15		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.7	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.94	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	124	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
		$T_j=125^\circ\text{C}$	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	6.5	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^\circ\text{C/W}$

ORDERING INFORMATION

J	ST	136	Q	-800	E
JieJie Microelectronics Co., Ltd.					
	Triacs				
		<u>I_T(RMS):4A</u>			
			<u>Q:TO-126</u>		
				<u>800:V_{DRM} / V_{RRM} ≥ 800V</u>	
					<u>E:I_{GT1-3} ≤ 10mA I_{GT4} ≤ 25mA</u>

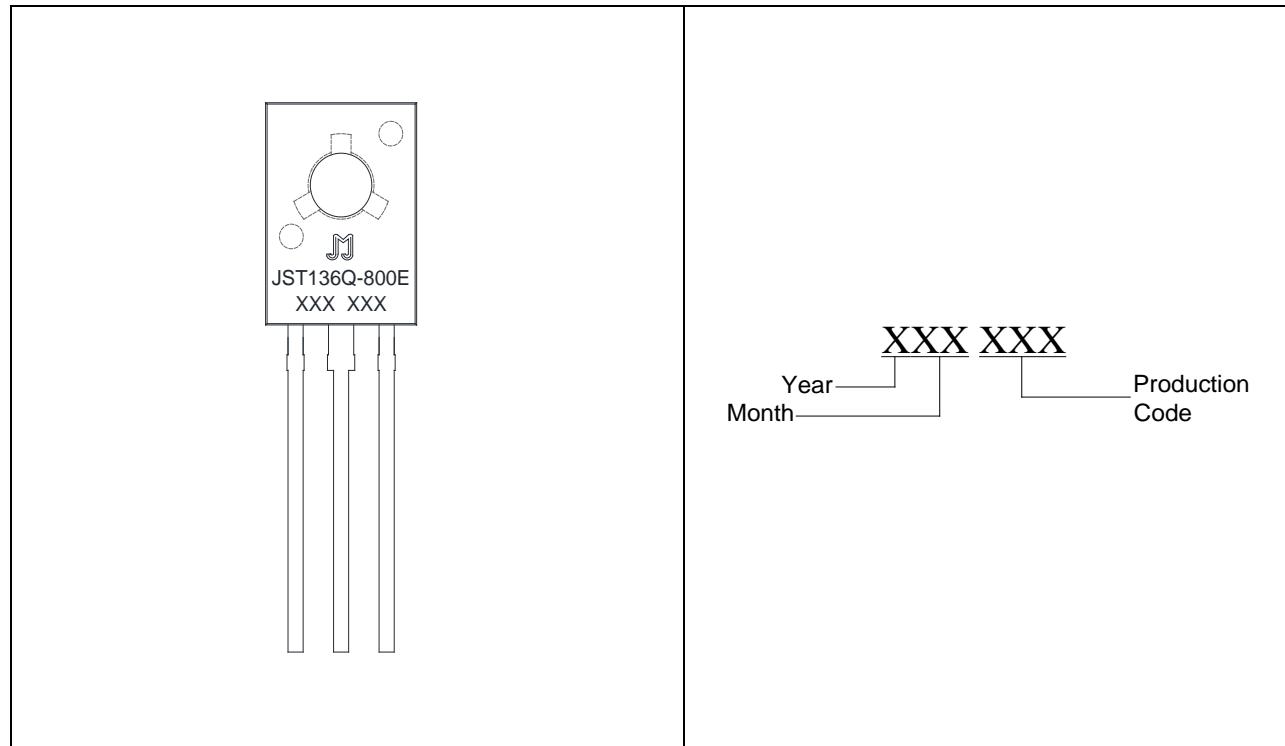
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

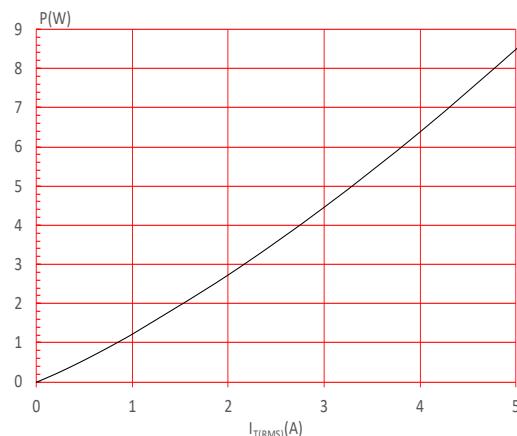


FIG.3: Surge peak on-state current versus number of cycles

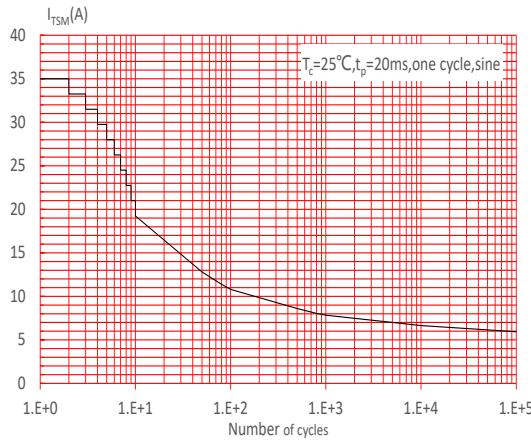


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t
(I - II - III: $\text{d}I/\text{d}t < 80\text{A}/\mu\text{s}$; IV: $\text{d}I/\text{d}t < 40\text{A}/\mu\text{s}$)

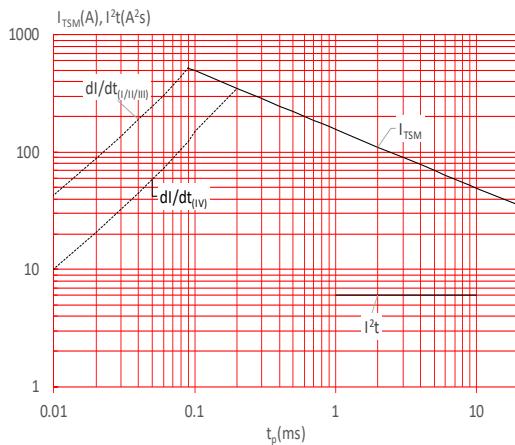


FIG.2: RMS on-state current versus case temperature

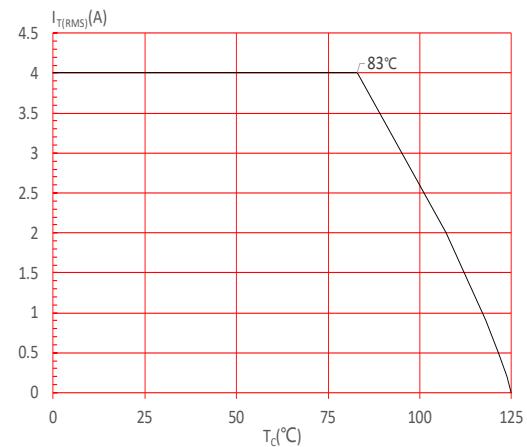


FIG.4: On-state characteristics

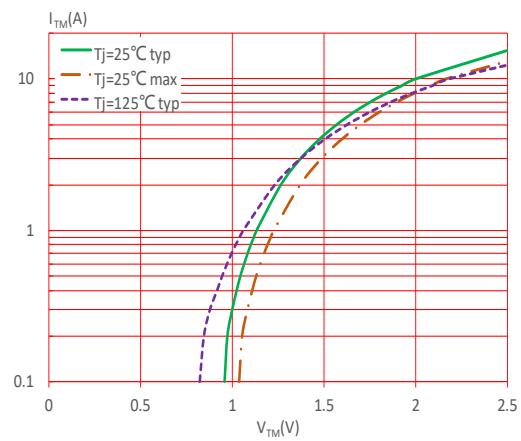


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

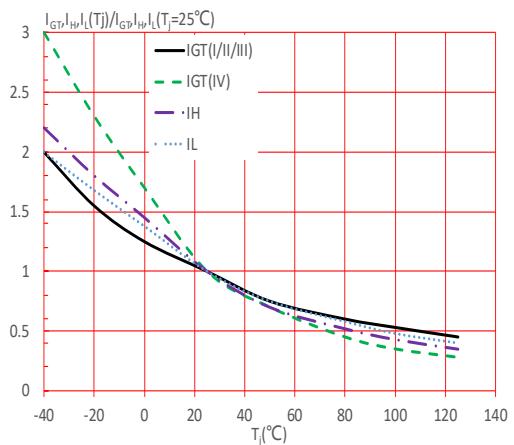
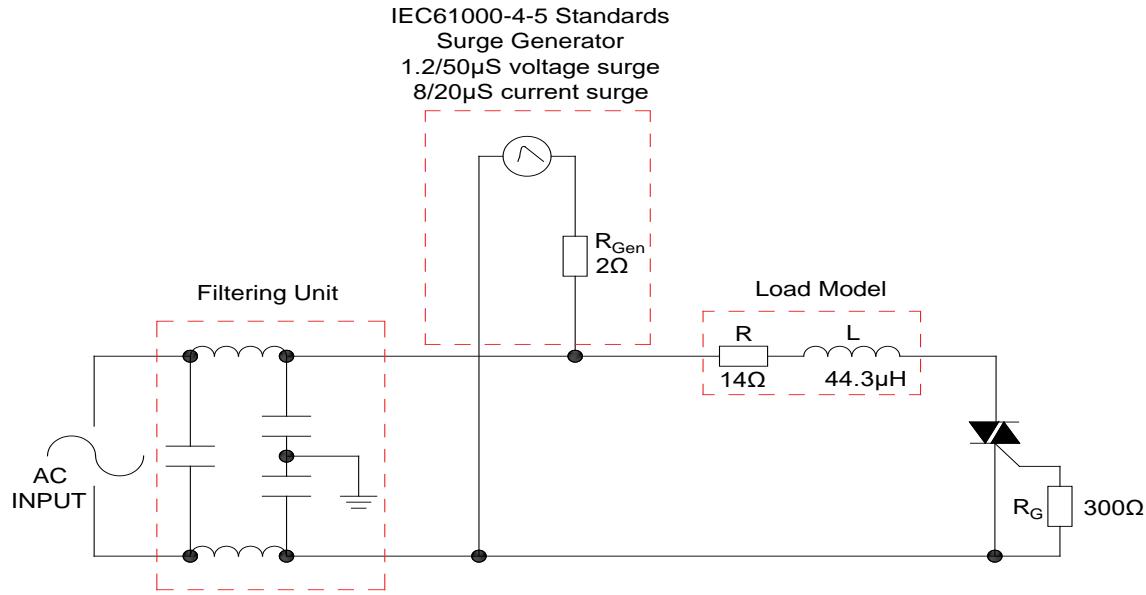


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

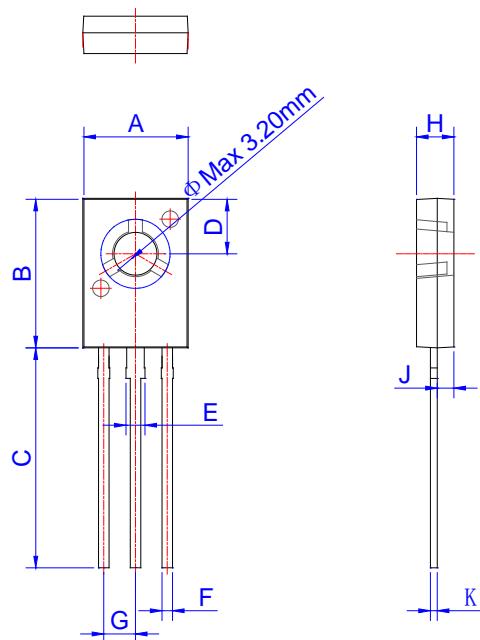
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
JST136Q-800E	800	10	25	TO-126	500	Bulk Pack

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G	2.15		2.45	0.085		0.096
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-126	Bulk Pack	500	2,000	10,000

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